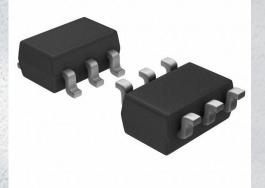


CPH6337-TL-E Datasheet

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DiGi Electronics Part Number

Manufacturer Product Number

Description

Manufacturer

Detailed Description

CPH6337-TL-E-DG

onsemi

CPH6337-TL-E

MOSFET P-CH 12V 3.5A 6CPH

P-Channel 12 V 3.5A (Ta) 1.6W (Ta) Surface Mount 6-CPH

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
CPH6337-TL-E	onsemi
Series:	Product Status:
	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (ld) @ 25°C:
12 V	3.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.8V, 4.5V	70mOhm @ 1.5A, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
1.4V @ 1mA	5.6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±10V	405 pF @ 6 V
FET Feature:	Power Dissipation (Max):
	1.6W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
6-СРН	SOT-23-6
Base Product Number:	
CPH633	

Environmental & Export classification

Moisture Sensitivity Level (MSL):
1 (Unlimited)
ECCN:
EAR99

REACH Status:	
REACH Unaffected	
HTSUS:	
3541.29.0095	

Power MOSFET -12V, 70mΩ, -3.5A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- High Speed Switching
- 1.8V drive
- Pb-Free and RoHS compliance
- Halogen Free compliance : CPH6337-TL-W

Typical Applications

Load Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-12	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	ID	-3.5	Α
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	-14	А
Power Dissipation When mounted on ceramic substrate $(1200 \text{mm}^2 \times 0.8 \text{mm})$	PD	1.6	w
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

be assumed, damage may occur and reliability may be affected.
2 : This product is designed to "ESD immunity<200V*", so please take care when handling.

*Machine Model

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1200mm ² × 0.8mm)	R _{θJA}	78.1	°C/W

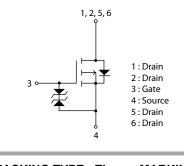


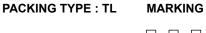
ON Semiconductor®

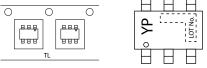
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VDSS	R _{DS} (on) Max	ID Max
	70mΩ@ –4.5V	
-12V	115mΩ@ –2.5V	-3.5A
	215mΩ@ –1.8V	









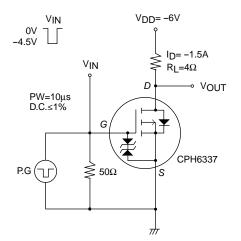
ORDERING INFORMATION

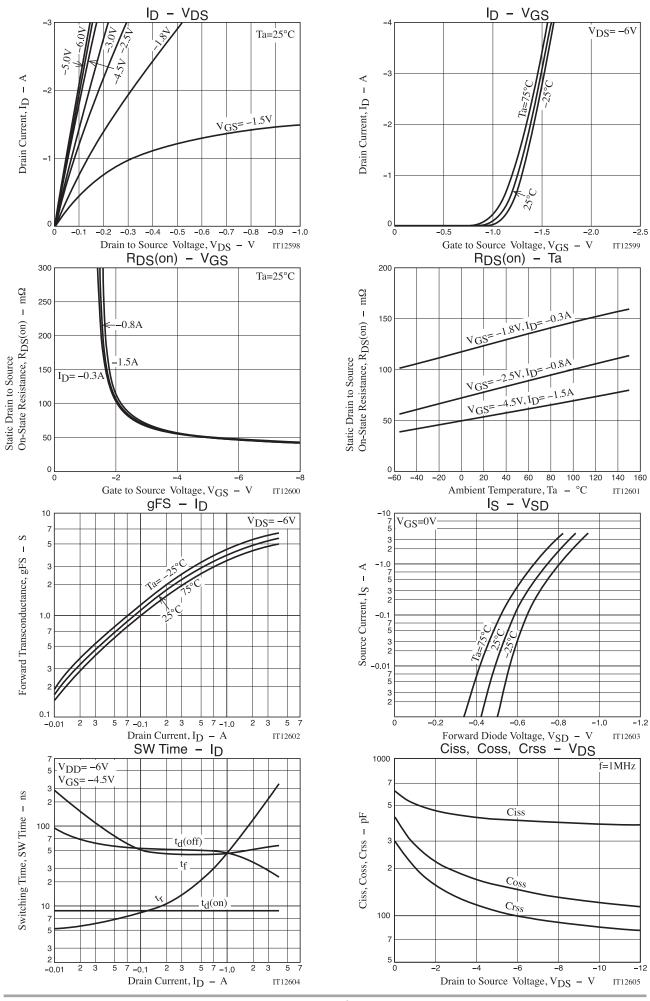
See detailed ordering and shipping information on page 5 of this data sheet.

Parameter	Symbol	Conditions	•		Value	
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transconductance	9FS	V _{DS} =-6V, I _D =-1.5A	2.7	4.5		S
	R _{DS} (on)1	ID=-1.5A, VGS=-4.5V		54	70	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	ID=-0.8A, VGS=-2.5V		80	115	mΩ
Resistance	R _{DS} (on)3	ID=-0.3A, VGS=-1.8V		125	215	mΩ
Input Capacitance	Ciss			405		pF
Output Capacitance	Coss	V _{DS} =–6V, f=1MHz		145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t _d (on)			8.8		ns
Rise Time	tr			80		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		41		ns
Fall Time	tf			50		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.6		nC
Forward Diode Voltage	V _{SD}	IS=-3.5A, VGS=0V		-0.86	-1.5	V

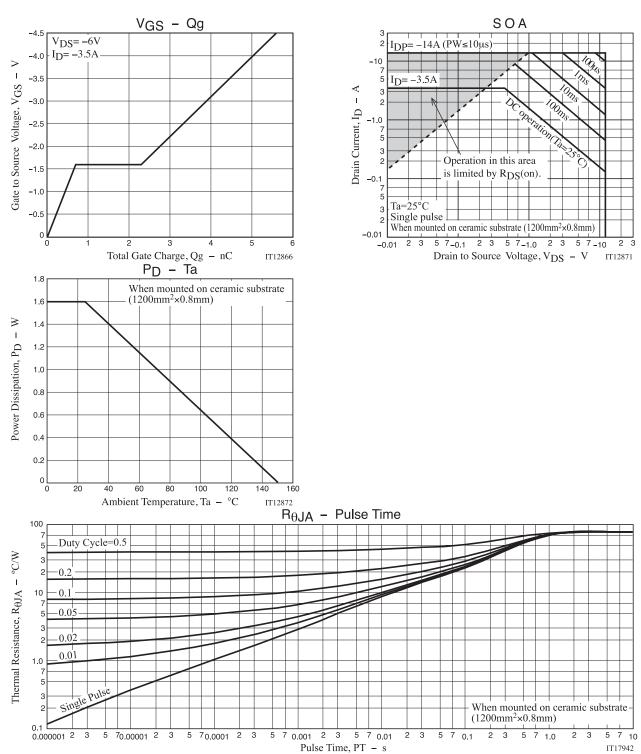
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





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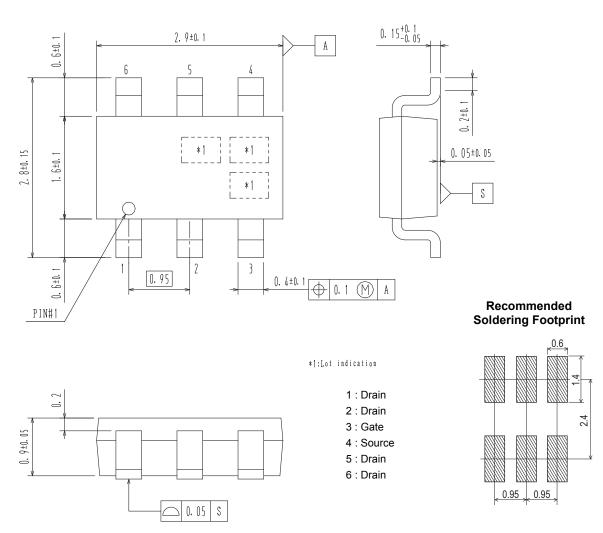


CPH6337

PACKAGE DIMENSIONS

unit : mm

CPH6 CASE 318BD ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
CPH6337-TL-E	YP	CPH6 (Pb-Free)	3,000 / Tape & Reel
CPH6337-TL-W		CPH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the CPH6337 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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